

REMARKS

In the Office Action, the Examiner rejected claims 1 and 7 under 35 U.S.C. § 102(e) as anticipated by Shukharev et al., U.S. Patent No. 6,147,012 ("Shukharev") and objected to claims 2, 3, 4, 5, and 6 as dependent upon a rejected base claim, but indicated that they would be allowable if rewritten in independent form to include all of the limitations of the base claim and any intervening claims.

Applicant thanks the Examiner for indicating allowable subject matter. By this Amendment, Applicant rewrites claim 2 in independent form including all the elements recited in claim 1. Accordingly, Applicant requests that the Examiner withdraw the objection to claim 2 and allow this claim. Claim 6 is allowable at least due to its dependence from allowable claim 2.

Furthermore, Applicant amends claims 3-5 to change their dependencies to allowable claim 2. Hence, claims 3-5 are allowable at least due to their dependence from allowable claim 2.

With regard to the rejection under 35 U.S.C. § 102(e), Applicant cancels claim 1 without prejudice or disclaimer of the subject matter thereof. Accordingly, the rejection of claim 1 is rendered moot. Furthermore, Applicant amends claim 7 to change its dependency to allowable claim 2. Thus, claim 7 is allowable at least due to its dependence from allowable claim 2.

In view of the foregoing, Applicant respectfully requests the reconsideration and reexamination of this application and the timely allowance of the pending claims.

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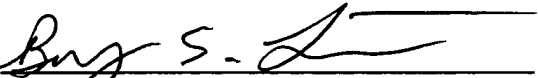
Attached hereto is a marked-up version of the changes made to the claims by this Amendment. The attachment is captioned "Appendix to Amendment of February 21, 2003".

Please grant any extensions of time required to enter this response and charge any additional required fees to our deposit account 06-0916.

Respectfully submitted,

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Appendix to Amendment of February 21, 2003

IN THE CLAIMS:

Please amend claims 3-5, and 7, as follows:

2. (Amended) [The method as recited in claim 1,] A method for manufacturing an interlayer dielectric layer, the method comprising the steps of:

a) setting an active matrix provided with a substrate and interconnections formed on the substrate in a chamber;

b) spraying a silicon source material and hydrogen peroxide (H₂O₂) in a gaseous state on the active matrix at a temperature ranging from approximately -20 °C to approximately 600 °C; and

c) forming the interlayer dielectric layer on the active matrix by a condensation reaction of the silicon source material and the H₂O₂ without performing a post thermal treatment,

wherein the silicon source material includes a tetra-ethyl-ortho-silicate (TEOS).

3. (Amended) The method as recited in claim [1]2, wherein [the silicon source material includes] the tetra-ethyl-ortho-silicate is a modified tetra-ethyl-ortho-silicate (TEOS).

4. (Amended) The method as recited in claim [1]2, wherein the step of spraying a silicon source material includes supplying simultaneously an inert gas when the silicon

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source material and the hydrogen peroxide (H₂O₂) are supplied into a flow rate controller.

5. (Amended) The method as recited in claim [1]2, wherein the step of spraying a silicon source material includes supplying simultaneously an inert gas when the silicon source material and the hydrogen peroxide (H₂O₂) are supplied into a distributor in the chamber.

7. (Twice Amended) The method as recited in claim [1]2, wherein a pressure in the chamber ranges from approximately 1 Torr to approximately 2 Torr.

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